

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

Claims 1-19 (previously cancelled)

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Claim 20 (Currently Amended): A method of removing photoresist material from surfaces formed on a semiconductor substrate, comprising:

providing a semiconductor substrate;

forming a low dielectric constant layer on a surface of the semiconductor substrate;

forming a hard mask layer over the low dielectric constant layer;

forming a photoresist layer over the hard mask layer;

forming an opening through an entire thickness of the photoresist layer and the hard mask layer exposing the low dielectric constant layer; and

removing the photoresist layer from over the hard mask layer with dimethyl sulfoxide of a high pressure liquid chromatography (HPLC) grade, the removing being performed after forming the opening through the entire thickness of the hard mask layer,

wherein a high selectivity of the dimethyl sulfoxide of HPLC grade toward a low dielectric constant material of the low dielectric constant layer causes the dimethyl sulfoxide of the HPLC grade to chemically dissolve the photoresist layer from over the hard mask layer without substantially damaging the low dielectric constant layer.

Claim 21 (Previously Presented): The method of claim 20, wherein the low dielectric constant material has a dielectric constant of about 3.0 or less.